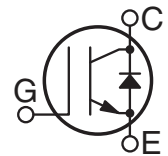
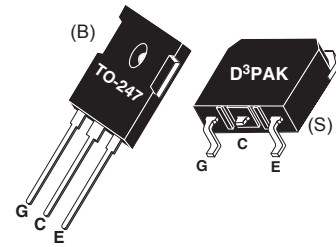


Utilizing the latest Field Stop and Trench Gate technologies, these IGBT's have ultra low  $V_{CE(ON)}$  and are ideal for low frequency applications that require absolute minimum conduction loss. Easy paralleling is a result of very tight parameter distribution and a slightly positive  $V_{CE(ON)}$  temperature coefficient. Low gate charge simplifies gate drive design and minimizes losses.

- 600V Field Stop
- Trench Gate: Low  $V_{CE(on)}$
- Easy Paralleling
- 6 $\mu$ s Short Circuit Capability
- 175°C Rated



**Applications: Welding, Inductive Heating, Solar Inverters, SMPS, Motor drives, UPS**


### MAXIMUM RATINGS

All Ratings:  $T_C = 25^\circ\text{C}$  unless otherwise specified.

Symbol	Parameter	APT20GN60B_SDQ2(G)	UNIT
$V_{CES}$	Collector-Emitter Voltage	600	Volts
$V_{GE}$	Gate-Emitter Voltage	$\pm 30$	
$I_{C1}$	Continuous Collector Current @ $T_C = 25^\circ\text{C}$	40	Amps
$I_{C2}$	Continuous Collector Current @ $T_C = 110^\circ\text{C}$	24	
$I_{CM}$	Pulsed Collector Current <sup>①</sup> @ $T_C = 175^\circ\text{C}$	60	
SSOA	Switching Safe Operating Area @ $T_J = 175^\circ\text{C}$	60A @ 600V	
$P_D$	Total Power Dissipation	136	Watts
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to 175	$^\circ\text{C}$
$T_L$	Max. Lead Temp. for Soldering: 0.063" from Case for 10 Sec.	300	

### STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	Units
$V_{(BR)CES}$	Collector-Emitter Breakdown Voltage ( $V_{GE} = 0V, I_C = 2mA$ )	600			Volts
$V_{GE(TH)}$	Gate Threshold Voltage ( $V_{CE} = V_{GE}, I_C = 290\mu A, T_J = 25^\circ\text{C}$ )	5.0	5.8	6.5	
$V_{CE(ON)}$	Collector-Emitter On Voltage ( $V_{GE} = 15V, I_C = 20A, T_J = 25^\circ\text{C}$ )	1.1	1.5	1.9	
	Collector-Emitter On Voltage ( $V_{GE} = 15V, I_C = 20A, T_J = 125^\circ\text{C}$ )		1.7		
$I_{CES}$	Collector Cut-off Current ( $V_{CE} = 600V, V_{GE} = 0V, T_J = 25^\circ\text{C}$ ) <sup>②</sup>			50	$\mu A$
	Collector Cut-off Current ( $V_{CE} = 600V, V_{GE} = 0V, T_J = 125^\circ\text{C}$ ) <sup>②</sup>			TBD	
$I_{GES}$	Gate-Emitter Leakage Current ( $V_{GE} = \pm 20V$ )			300	nA
$R_{G(int)}$	Integrated Gate Resistor		N/A		$\Omega$

 **CAUTION:** These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

## DYNAMIC CHARACTERISTICS

APT20GN60B\_SDQ2(G)

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT	
$C_{ies}$	Input Capacitance	<b>Capacitance</b> $V_{GE} = 0V, V_{CE} = 25V$ $f = 1 \text{ MHz}$		1110		pF	
$C_{oes}$	Output Capacitance			50			
$C_{res}$	Reverse Transfer Capacitance			35			
$V_{GEP}$	Gate-to-Emitter Plateau Voltage	<b>Gate Charge</b> $V_{GE} = 15V$ $V_{CE} = 300V$ $I_C = 20A$		9.5		V	
$Q_g$	Total Gate Charge <sup>③</sup>			120			
$Q_{ge}$	Gate-Emitter Charge			10			
$Q_{gc}$	Gate-Collector ("Miller") Charge			70			
SSOA	Switching Safe Operating Area	$T_J = 175^\circ\text{C}, R_G = 4.3\Omega$ <sup>⑦</sup> , $V_{GE} = 15V, L = 100\mu\text{H}, V_{CE} = 600V$	60			A	
SCSOA	Short Circuit Safe Operating Area	$V_{CC} = 360V, V_{GE} = 15V,$ $T_J = 150^\circ\text{C}, R_G = 4.3\Omega$ <sup>⑦</sup>	6			$\mu\text{s}$	
$t_{d(on)}$	Turn-on Delay Time	<b>Inductive Switching (25°C)</b>  $V_{CC} = 400V$ $V_{GE} = 15V$ $I_C = 20A$ $R_G = 4.3\Omega$ <sup>⑦</sup> $T_J = +25^\circ\text{C}$		9		ns	
$t_r$	Current Rise Time			10			
$t_{d(off)}$	Turn-off Delay Time			140			
$t_f$	Current Fall Time			95			
$E_{on1}$	Turn-on Switching Energy <sup>④</sup>				230		$\mu\text{J}$
$E_{on2}$	Turn-on Switching Energy (Diode) <sup>⑤</sup>				350		
$E_{off}$	Turn-off Switching Energy <sup>⑥</sup>				580		
$t_{d(on)}$	Turn-on Delay Time		<b>Inductive Switching (125°C)</b>  $V_{CC} = 400V$ $V_{GE} = 15V$ $I_C = 20A$ $R_G = 4.3\Omega$ <sup>⑦</sup> $T_J = +125^\circ\text{C}$		9		ns
$t_r$	Current Rise Time				10		
$t_{d(off)}$	Turn-off Delay Time				160		
$t_f$	Current Fall Time			130			
$E_{on1}$	Turn-on Switching Energy <sup>④</sup>				250		$\mu\text{J}$
$E_{on2}$	Turn-on Switching Energy (Diode) <sup>⑤</sup>				690		
$E_{off}$	Turn-off Switching Energy <sup>⑥</sup>				750		

## THERMAL AND MECHANICAL CHARACTERISTICS

Symbol	Characteristic	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to Case ( <b>IGBT</b> )			1.1	$^\circ\text{C/W}$
$R_{\theta JC}$	Junction to Case ( <b>DIODE</b> )			.80	
$W_T$	Package Weight		5.9		gm

① Repetitive Rating: Pulse width limited by maximum junction temperature.

② For Combi devices,  $I_{ces}$  includes both IGBT and FRED leakages

③ See MIL-STD-750 Method 3471.

④  $E_{on1}$  is the clamped inductive turn-on energy of the IGBT only, without the effect of a commutating diode reverse recovery current adding to the IGBT turn-on loss. Tested in inductive switching test circuit shown in figure 21, but with a Silicon Carbide diode.

⑤  $E_{on2}$  is the clamped inductive turn-on energy that includes a commutating diode reverse recovery current in the IGBT turn-on switching loss. (See Figures 21, 22.)

⑥  $E_{off}$  is the clamped inductive turn-off energy measured in accordance with JEDEC standard JESD24-1. (See Figures 21, 23.)

⑦  $R_G$  is external gate resistance, not including  $R_{G(int)}$  nor gate driver impedance. (MIC4452)

Microsemi Reserves the right to change, without notice, the specifications and information contained herein.

TYPICAL PERFORMANCE CURVES

APT20GN60B\_SDQ2(G)

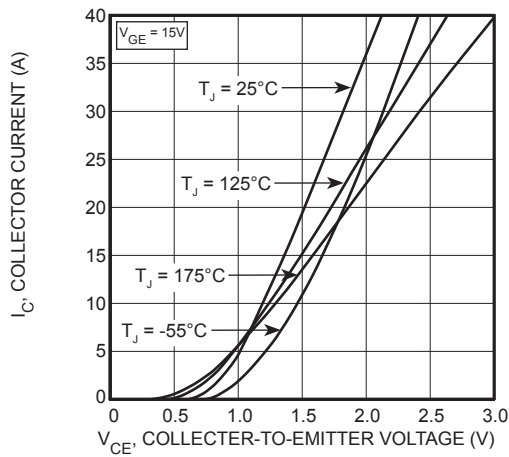


FIGURE 1, Output Characteristics ( $T_J = 25^\circ\text{C}$ )

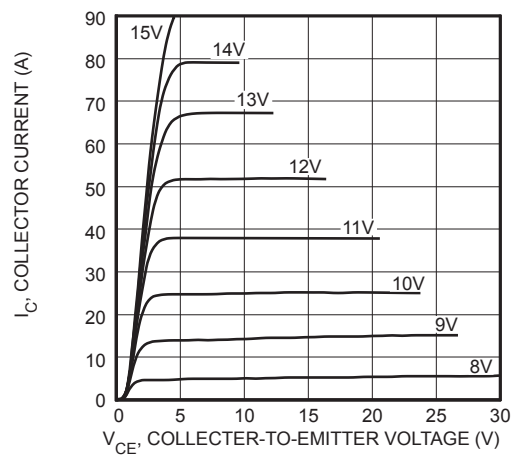


FIGURE 2, Output Characteristics ( $T_J = 125^\circ\text{C}$ )

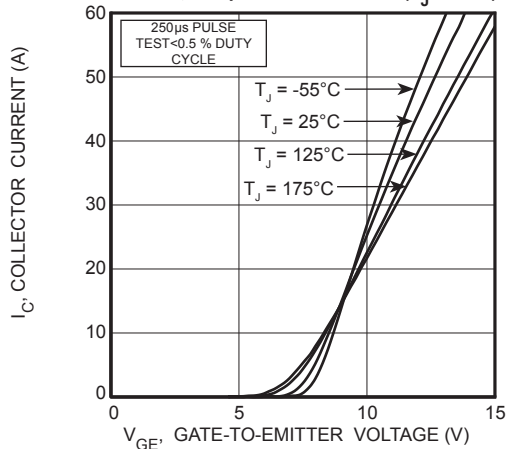


FIGURE 3, Transfer Characteristics

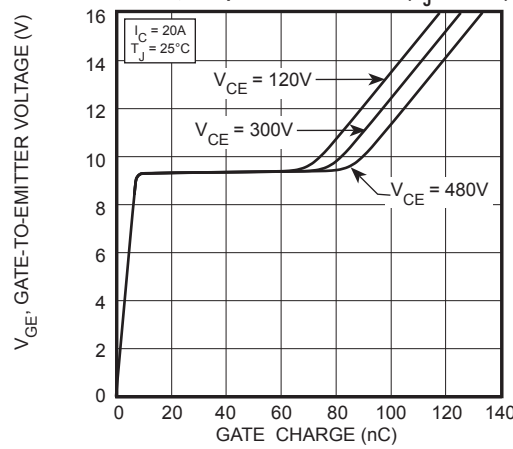


FIGURE 4, Gate Charge

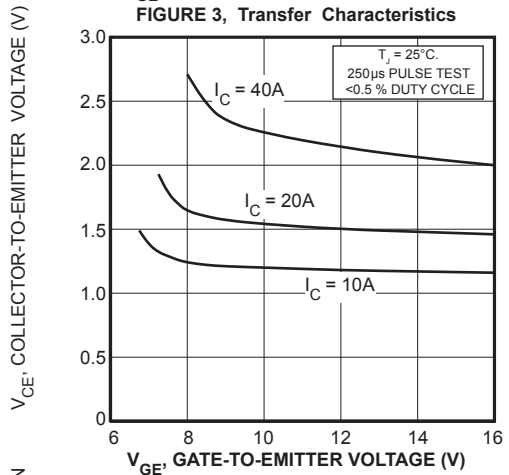


FIGURE 5, On State Voltage vs Gate-to-Emitter Voltage

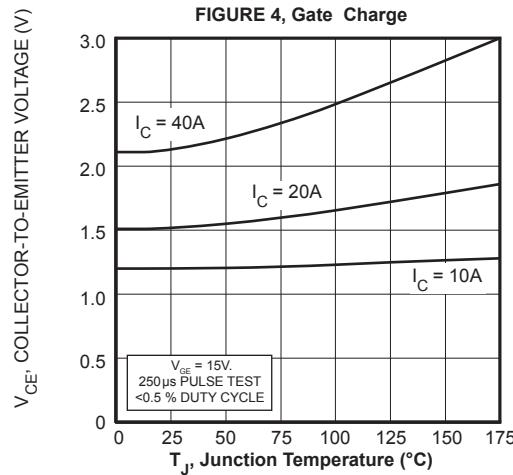


FIGURE 6, On State Voltage vs Junction Temperature

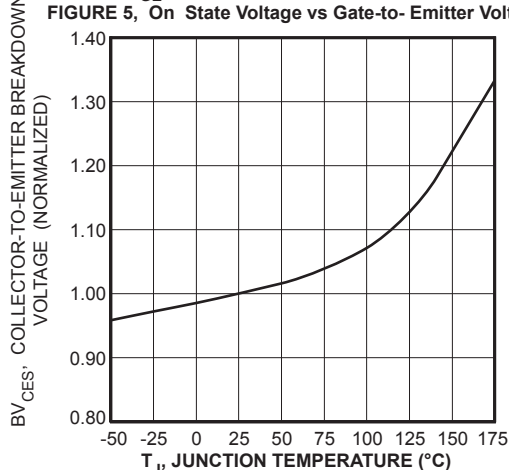


FIGURE 7, Breakdown Voltage vs. Junction Temperature

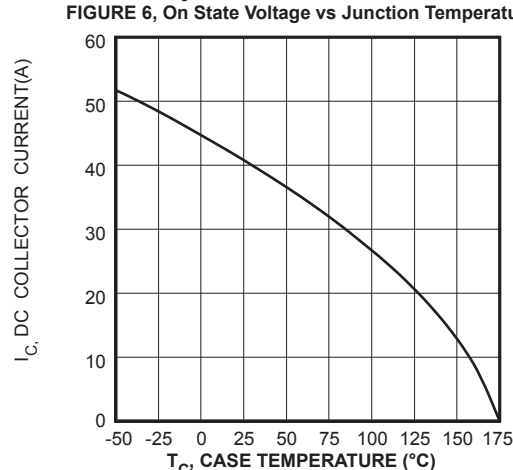


FIGURE 8, DC Collector Current vs Case Temperature

TYPICAL PERFORMANCE CURVES

APT20GN60B\_SDQ2(G)

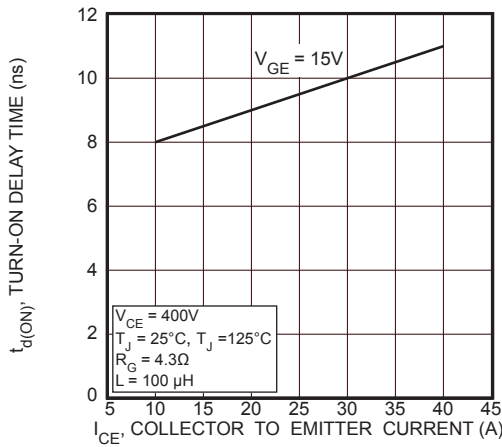


FIGURE 9, Turn-On Delay Time vs Collector Current

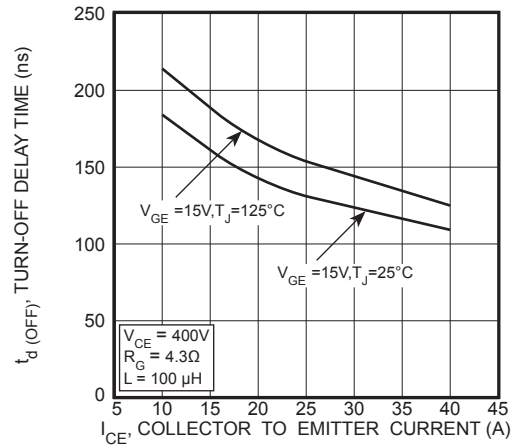


FIGURE 10, Turn-Off Delay Time vs Collector Current

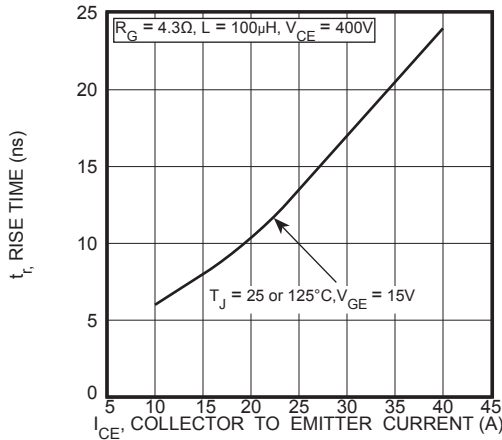


FIGURE 11, Current Rise Time vs Collector Current

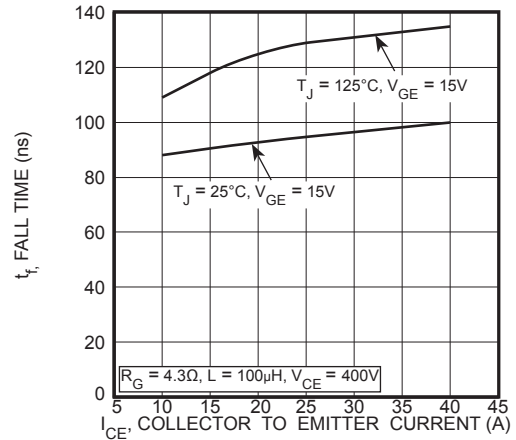


FIGURE 12, Current Fall Time vs Collector Current

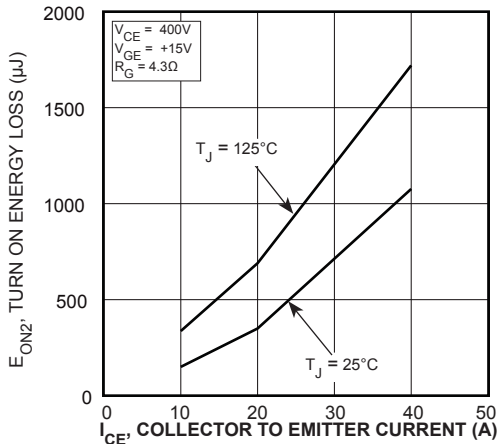


FIGURE 13, Turn-On Energy Loss vs Collector Current

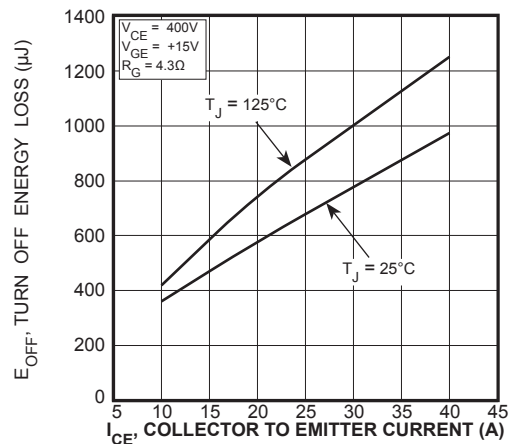


FIGURE 14, Turn Off Energy Loss vs Collector Current

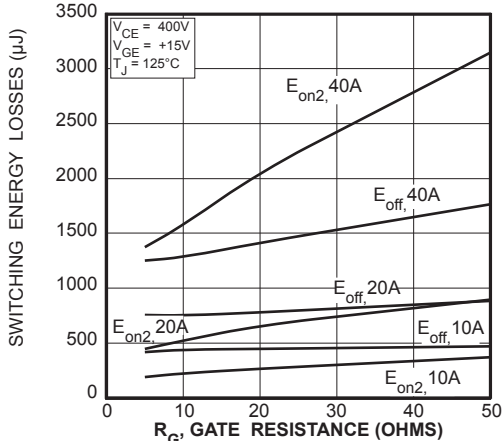


FIGURE 15, Switching Energy Losses vs. Gate Resistance

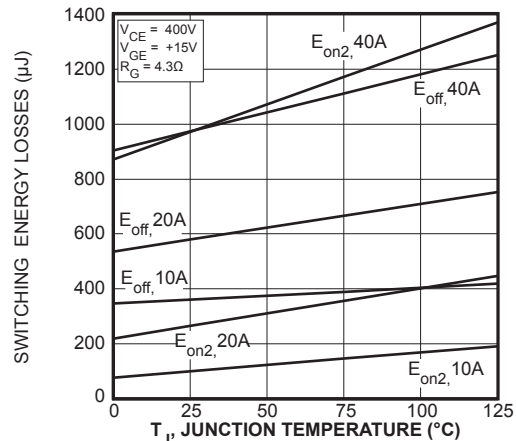


FIGURE 16, Switching Energy Losses vs Junction Temperature

TYPICAL PERFORMANCE CURVES

APT20GN60B\_SDQ2(G)

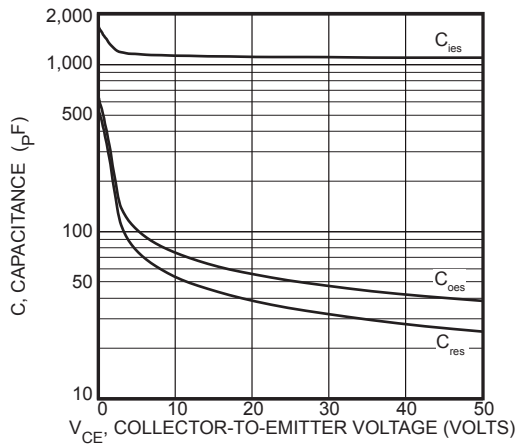


Figure 17, Capacitance vs Collector-To-Emitter Voltage

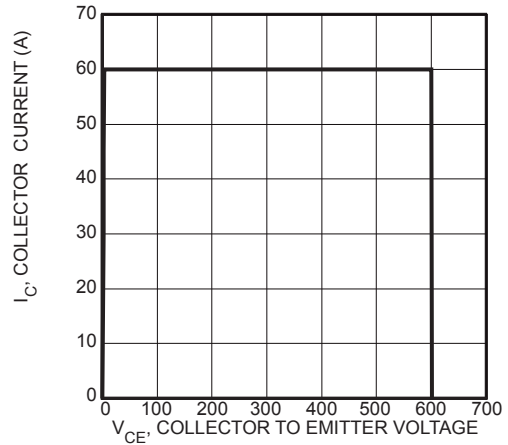


Figure 18, Minimum Switching Safe Operating Area

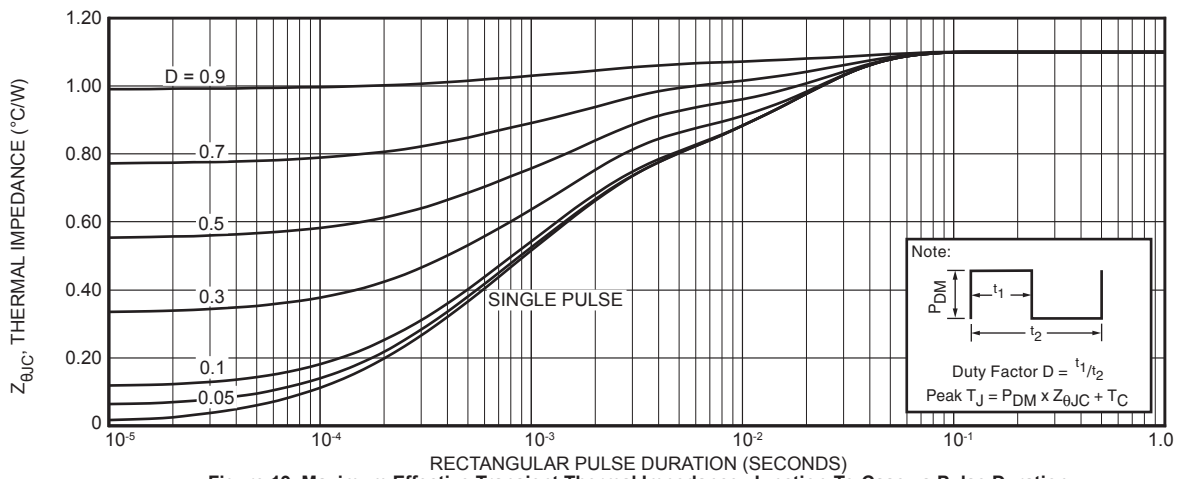


Figure 19, Maximum Effective Transient Thermal Impedance, Junction-To-Case vs Pulse Duration

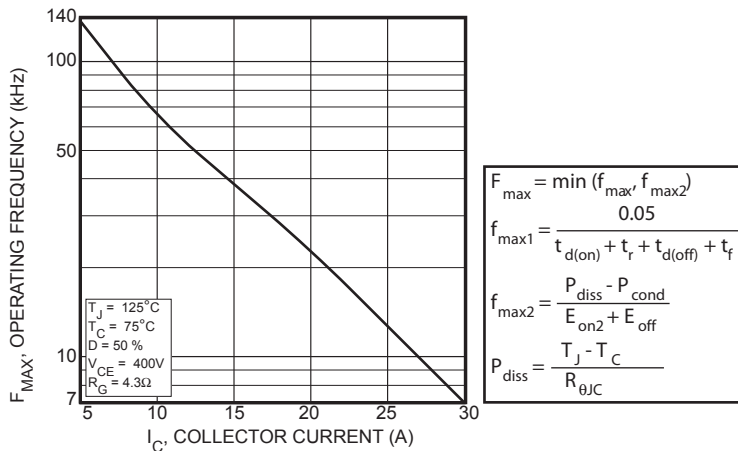


Figure 20, Operating Frequency vs Collector Current

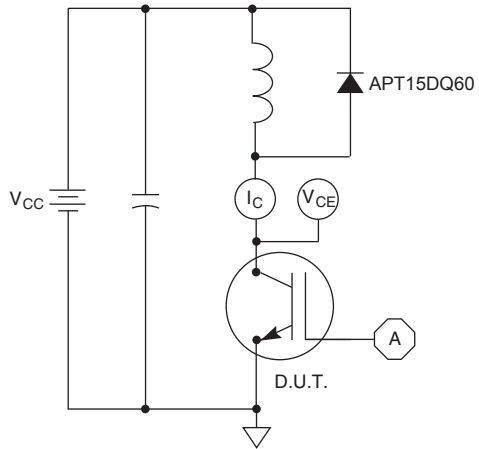


Figure 21, Inductive Switching Test Circuit

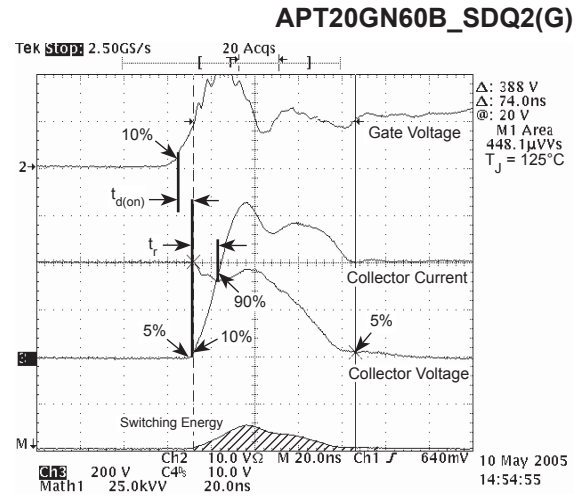


Figure 22, Turn-on Switching Waveforms and Definitions

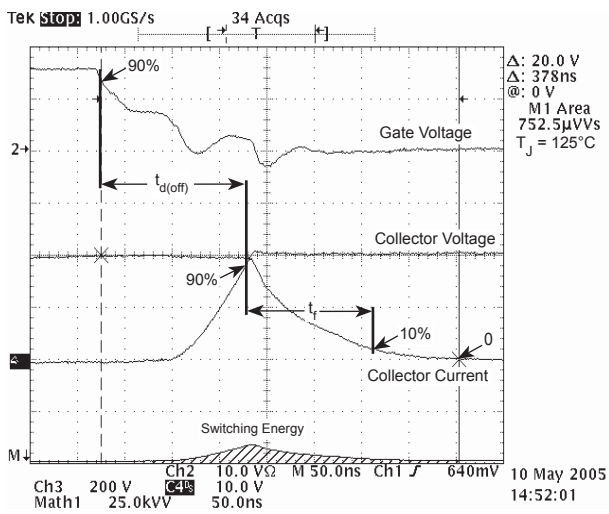


Figure 23, Turn-off Switching Waveforms and Definitions

# ULTRAFAST SOFT RECOVERY ANTI-PARALLEL DIODE

**MAXIMUM RATINGS**

All Ratings:  $T_C = 25^\circ\text{C}$  unless otherwise specified.

Symbol	Characteristic / Test Conditions	APT20GN60B_SDQ2(G)		UNIT
$I_{F(AV)}$	Maximum Average Forward Current ( $T_C = 117^\circ\text{C}$ , Duty Cycle = 0.5)		30	Amps
$I_{F(RMS)}$	RMS Forward Current (Square wave, 50% duty)		51	
$I_{FSM}$	Non-Repetitive Forward Surge Current ( $T_J = 45^\circ\text{C}$ , 8.3ms)		320	

**STATIC ELECTRICAL CHARACTERISTICS**

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
$V_F$	Forward Voltage	$I_F = 30\text{A}$	2.0		Volts
		$I_F = 60\text{A}$	2.4		
		$I_F = 30\text{A}, T_J = 125^\circ\text{C}$	1.7		

**DYNAMIC CHARACTERISTICS**

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
$t_{rr}$	Reverse Recovery Time	$I_F = 1\text{A}, di_F/dt = -100\text{A}/\mu\text{s}, V_R = 30\text{V}, T_J = 25^\circ\text{C}$	-	23		ns
$t_{rr}$	Reverse Recovery Time	$I_F = 30\text{A}, di_F/dt = -200\text{A}/\mu\text{s}, V_R = 400\text{V}, T_C = 25^\circ\text{C}$	-	30		
$Q_{rr}$	Reverse Recovery Charge		-	55		nC
$I_{RRM}$	Maximum Reverse Recovery Current		-	3	-	Amps
$t_{rr}$	Reverse Recovery Time	$I_F = 30\text{A}, di_F/dt = -200\text{A}/\mu\text{s}, V_R = 400\text{V}, T_C = 125^\circ\text{C}$	-	175		ns
$Q_{rr}$	Reverse Recovery Charge		-	485		nC
$I_{RRM}$	Maximum Reverse Recovery Current		-	6	-	Amps
$t_{rr}$	Reverse Recovery Time	$I_F = 30\text{A}, di_F/dt = -1000\text{A}/\mu\text{s}, V_R = 400\text{V}, T_C = 125^\circ\text{C}$	-	75		ns
$Q_{rr}$	Reverse Recovery Charge		-	855		nC
$I_{RRM}$	Maximum Reverse Recovery Current		-	22		Amps

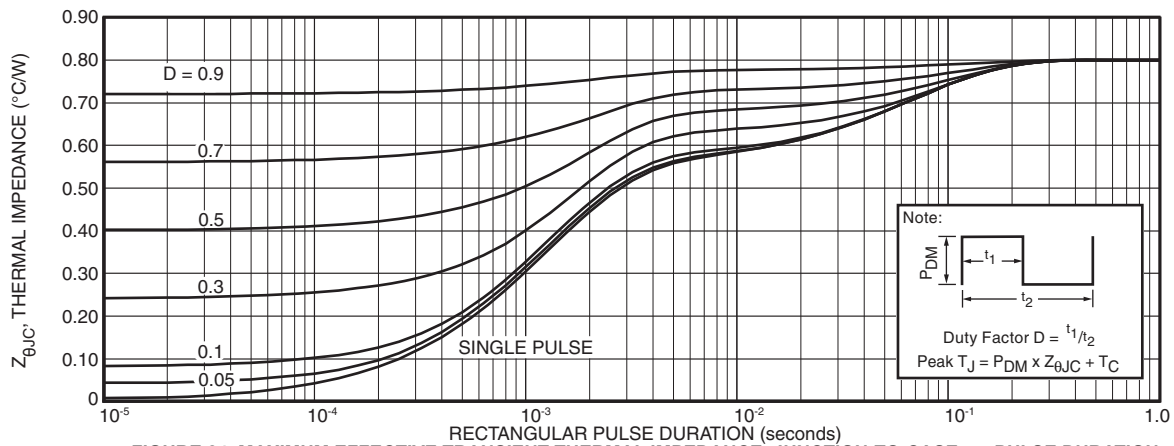


FIGURE 24. MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs. PULSE DURATION

TYPICAL PERFORMANCE CURVES

APT20GN60B\_SDQ2(G)

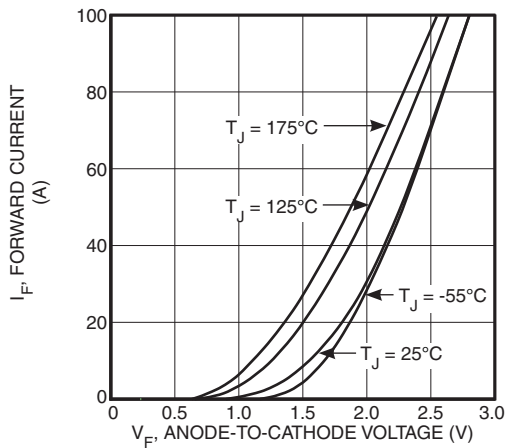


Figure 25. Forward Current vs. Forward Voltage

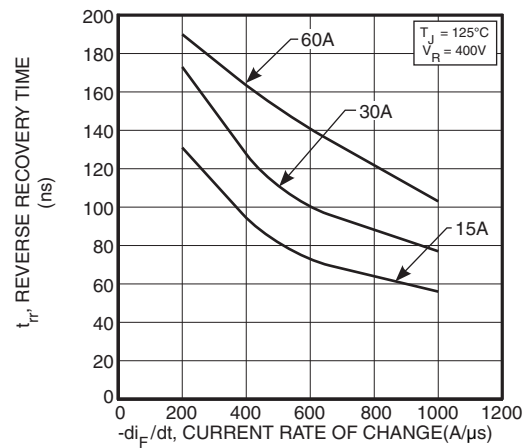


Figure 26. Reverse Recovery Time vs. Current Rate of Change

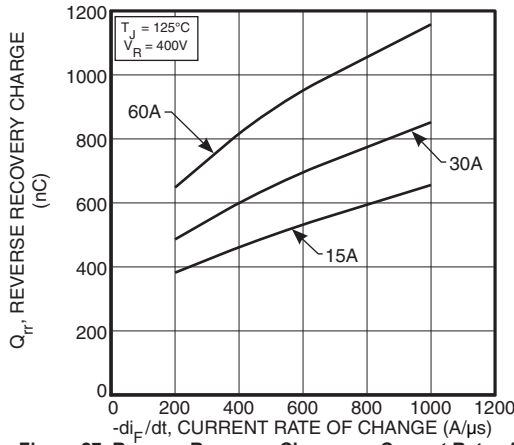


Figure 27. Reverse Recovery Charge vs. Current Rate of Change

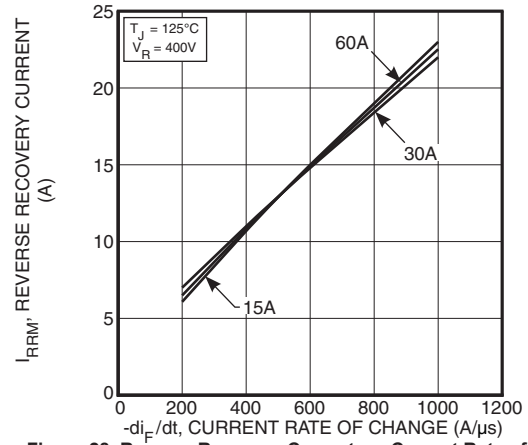


Figure 28. Reverse Recovery Current vs. Current Rate of Change

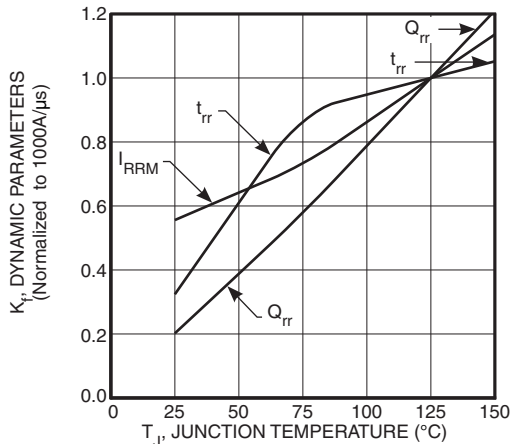


Figure 29. Dynamic Parameters vs. Junction Temperature

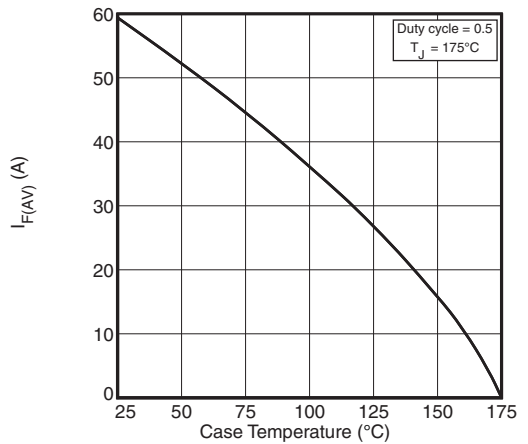


Figure 30. Maximum Average Forward Current vs. Case Temperature

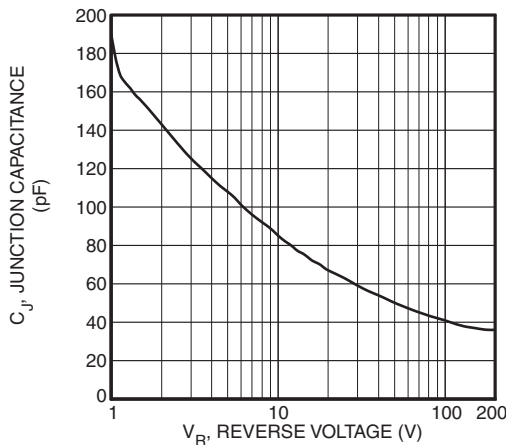


Figure 31. Junction Capacitance vs. Reverse Voltage



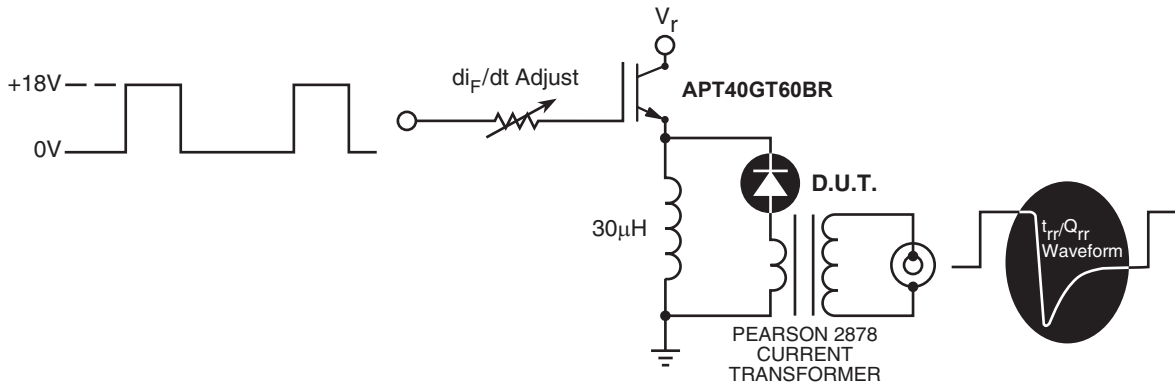


Figure 32. Diode Test Circuit

- 1  $I_F$  - Forward Conduction Current
- 2  $di_F/dt$  - Rate of Diode Current Change Through Zero Crossing.
- 3  $I_{RRM}$  - Maximum Reverse Recovery Current.
- 4  $t_{rr}$  - Reverse Recovery Time, measured from zero crossing where diode current goes from positive to negative, to the point at which the straight line through  $I_{RRM}$  and  $0.25 \cdot I_{RRM}$  passes through zero.
- 5  $Q_{rr}$  - Area Under the Curve Defined by  $I_{RRM}$  and  $t_{rr}$ .

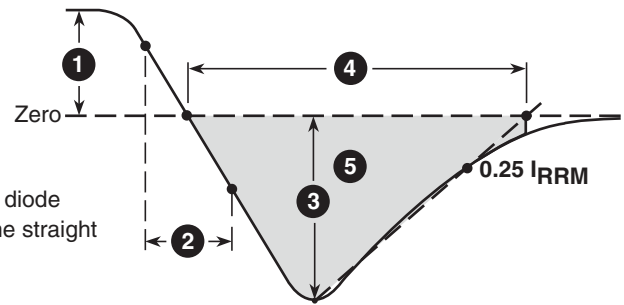
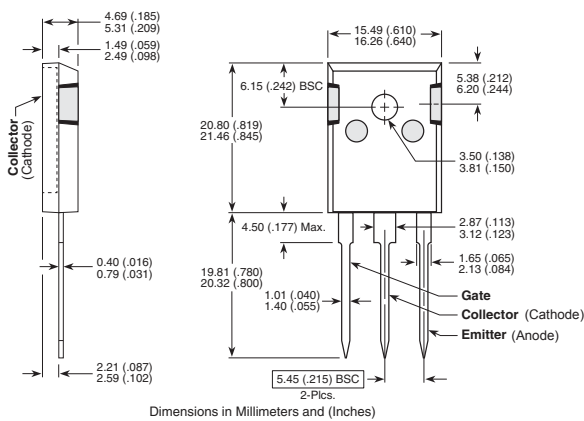


Figure 32, Diode Reverse Recovery Waveform and Definitions

**TO-247 Package Outline**

Ⓔ1 SAC: Tin, Silver, Copper



**D<sup>3</sup>PAK Package Outline**

Ⓔ3 100% Pure Tin

